Hideo Ohno

List of Publications by Year
in descending order

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764 papers	65,704 citations	2832 97 h-index	1256 232 g-index
781 all docs	781 docs citations	781 times ranked	26372 citing authors

#	Article	IF	Citations
1	Memristive control of mutual spin Hall nano-oscillator synchronization for neuromorphic computing. Nature Materials, 2022, 21, 81-87.	13.3	63
2	Hardware-Aware In Situ Learning Based on Stochastic Magnetic Tunnel Junctions. Physical Review Applied, 2022, 17, .	1.5	36
3	Nanometer-thin L1-MnAl film with B2-CoAl underlayer for high-speed and high-density STT-MRAM: Structure and magnetic properties. Applied Physics Letters, 2022, 120, .	1.5	6
4	Generalized scaling of spin qubit coherence in over 12,000 host materials. Proceedings of the National Academy of Sciences of the United States of America, 2022, 119, e2121808119.	3.3	38
5	Observation of domain structure in non-collinear antiferromagnetic Mn3Sn thin films by magneto-optical Kerr effect. Applied Physics Letters, 2022, 120, .	1.5	12
6	Local bifurcation with spin-transfer torque in superparamagnetic tunnel junctions. Nature Communications, 2022, 13, .	5.8	3
7	Dual-Port SOT-MRAM Achieving 90-MHz Read and 60-MHz Write Operations Under Field-Assistance-Free Condition. IEEE Journal of Solid-State Circuits, 2021, 56, 1116-1128.	3.5	24
8	Temperature dependence of the energy barrier in X/1X nm shape-anisotropy magnetic tunnel junctions. Applied Physics Letters, 2021, 118, .	1.5	10
9	Dilute Magnetic Materials. , 2021, , 1-56.		1
10	Coherent magnetization reversal of a cylindrical nanomagnet in shape-anisotropy magnetic tunnel junctions. Applied Physics Letters, 2021, 118, .	1.5	5
11	Theory of relaxation time of stochastic nanomagnets. Physical Review B, 2021, 103, .	1.1	20
12	Nanosecond Random Telegraph Noise in In-Plane Magnetic Tunnel Junctions. Physical Review Letters, 2021, 126, 117202.	2.9	64
13	Field-free and sub-ns magnetization switching of magnetic tunnel junctions by combining spin-transfer torque and spinâ€“orbit torque. Applied Physics Letters, 2021, 118, .	1.5	26
14	Double-Free-Layer Magnetic Tunnel Junctions for Probabilistic Bits. Physical Review Applied, 2021, 15, .	1.5	15
15	Chiral-spin rotation of non-collinear antiferromagnet by spinâ€“orbit torque. Nature Materials, 2021, 20, 1364-1370.	13.3	87
16	Electrically connected spin-torque oscillators array for 2.4â€‰GHz WiFi band transmission and energy harvesting. Nature Communications, 2021, 12, 2924.	5.8	40
17	Correlation of anomalous Hall effect with structural parameters and magnetic ordering in Mn3+xSn1â^’x thin films. AIP Advances, 2021, 11, .	0.6	14
18	Influence of domain wall anisotropy on the current-induced hysteresis loop shift for quantification of the Dzyaloshinskii-Moriya interaction. Physical Review B, 2021, 103, .	1.1	8

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19	Unconventional Hall effect and its variation with Co-doping in van der Waals Fe3GeTe2. Scientific Reports, 2021, 11, 14121.	1.6	13
20	Magnetization processes and magnetic domain structures in Ta/CoFeB/MgO stacks. Journal of Magnetism and Magnetic Materials, 2021, 529, 167699.	1.0	5
21	Sigmoidal curves of stochastic magnetic tunnel junctions with perpendicular easy axis. Applied Physics Letters, 2021, 119, .	1.5	10
22	Dilute Magnetic Materials. , 2021, , 923-978.		0
23	Fast Switching Down to 3.5 ns in Sub-5-nm Magnetic Tunnel Junctions Achieved by Engineering Relaxation Time. , 2021, , .		5
24	Temperature dependence of intrinsic critical current in perpendicular easy axis CoFeB/MgO magnetic tunnel junctions. Applied Physics Letters, 2021, 119, .	1.5	8
25	Crystal orientation and anomalous Hall effect of sputter-deposited non-collinear antiferromagnetic Mn₃Sn thin films. Applied Physics Express, 2020, 13, 013001.	1.1	24
26	Energy Efficient Control of Ultrafast Spin Current to Induce Single Femtosecond Pulse Switching of a Ferromagnet. Advanced Science, 2020, 7, 2001996.	5.6	30
27	Multidomain Memristive Switching of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mi>Pt</mml:mi><mml:mn>38</mml:mn></mml:msub><mml:msub><mml:mi>Mn</mml:mi><mml:mi><m stretchy="false">[</mml:mo><mml:mi>Co</mml:mi><mml:mo>/</mml:mo><mml:mi>Ni</mml:mi><mml:msub><mml:mo stretchy="false">]</mml:mo><mml:mi>n</mml:mi></mml:msub></mml:math> Multilayers. Physical Review Applied, 2020, 14, .	1.5	10
28	Probing edge condition of nanoscale CoFeB/MgO magnetic tunnel junctions by spin-wave resonance. Applied Physics Letters, 2020, 117, 202404.	1.5	3
29	Engineering Single-Shot All-Optical Switching of Ferromagnetic Materials. Nano Letters, 2020, 20, 8654-8660.	4.5	37
30	Spin-orbit torque switching of an antiferromagnetic metallic heterostructure. Nature Communications, 2020, 11, 5715.	5.8	49
31	Giant voltage-controlled modulation of spin Hall nano-oscillator damping. Nature Communications, 2020, 11, 4006.	5.8	48
32	Dual-Port Field-Free SOT-MRAM Achieving 90-MHz Read and 60-MHz Write Operations under 55-nm CMOS Technology and 1.2-V Supply Voltage. , 2020, , .		15
33	Complex switching behavior of magnetostatically coupled single-domain nanomagnets probed by micro-Hall magnetometry. Applied Physics Letters, 2020, 116, .	1.5	4
34	Zero-field spin precession dynamics of high-mobility two-dimensional electron gas in persistent spin helix regime. Physical Review B, 2020, 101, .	1.1	4
35	Visualizing Magnetic Structure in 3D Nanoscale Niâ€“Fe Gyroid Networks. Nano Letters, 2020, 20, 3642-3650.	4.5	25
36	Probabilistic computing based on spintronics technology. , 2020, , .		1

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37	Neuromorphic computing with antiferromagnetic spintronics. Journal of Applied Physics, 2020, 128, .	1.1	40
38	Composition dependence of spinâ^'orbit torque in Pt1â^'xMnx/CoFeB heterostructures. Applied Physics Letters, 2020, 117, .	1.5	8
39	Current distribution in metallic multilayers from resistance measurements. Physical Review B, 2020, 101, .	1.1	6
40	Scaling magnetic tunnel junction down to single-digit nanometersâ€"Challenges and prospects. Applied Physics Letters, 2020, 116, .	1.5	49
41	High-Performance Shape-Anisotropy Magnetic Tunnel Junctions down to 2.3 nm. , 2020, , .		31
42	Spin-Pumping-Free Determination of Spin-Orbit Torque Efficiency from Spin-Torque Ferromagnetic Resonance. Physical Review Applied, 2019, 12, .	1.5	23
43	A 47.14-$muext{W}$ 200-MHz MOS/MTJ-Hybrid Nonvolatile Microcontroller Unit Embedding STT-MRAM and FPGA for IoT Applications. IEEE Journal of Solid-State Circuits, 2019, 54, 2991-3004.	3.5	39
44	Families of magnetic semiconductors â€" an overview. Journal of Semiconductors, 2019, 40, 080301.	2.0	52
45	Properties of sputtered full Heusler alloy Cr₂MnSb and its application in a magnetic tunnel junction. Journal Physics D: Applied Physics, 2019, 52, 495002.	1.3	8
46	Magnetization dynamics and related phenomena in semiconductors with ferromagnetism. Journal of Semiconductors, 2019, 40, 081502.	2.0	1
47	Write-error rate of nanoscale magnetic tunnel junctions in the precessional regime. Applied Physics Letters, 2019, 115, .	1.5	7
48	Formation and current-induced motion of synthetic antiferromagnetic skyrmion bubbles. Nature Communications, 2019, 10, 5153.	5.8	165
49	Spin-transfer-torque magnetoresistive random-access memory (STT-MRAM) technology. , 2019, , 237-281.		7
50	Neuromorphic Computing: Artificial Neuron and Synapse Realized in an Antiferromagnet/Ferromagnet Heterostructure Using Dynamics of Spinâ€"Orbit Torque Switching (Adv. Mater. 23/2019). Advanced Materials, 2019, 31, 1970167.	11.1	1
51	Artificial Neuron and Synapse Realized in an Antiferromagnet/Ferromagnet Heterostructure Using Dynamics of Spinâ€"Orbit Torque Switching. Advanced Materials, 2019, 31, e1900636.	11.1	124
52	Reversal of domain wall chirality with ferromagnet thickness in W/(Co)FeB/MgO systems. Applied Physics Letters, 2019, 114, .	1.5	8
53	First demonstration of field-free SOT-MRAM with 0.35 ns write speed and 70 thermal stability under 400Â°C thermal tolerance by canted SOT structure and its advanced patterning/SOT channel technology. , 2019, , .		41
54	Stack structure and temperature dependence of spin-orbit torques in heterostructures with antiferromagnetic PtMn. Applied Physics Letters, 2019, 115, .	1.5	9

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55	Integer factorization using stochastic magnetic tunnel junctions. Nature, 2019, 573, 390-393.	13.7	298
56	Spin-orbit torque-induced switching of in-plane magnetized elliptic nanodot arrays with various easy-axis directions measured by differential planar Hall resistance. Applied Physics Letters, 2019, 114, 012410.	1.5	20
57	Giant perpendicular magnetic anisotropy in Ir/Co/Pt multilayers. Physical Review Materials, 2019, 3, .	0.9	29
58	Spin transport and spin torque in antiferromagnetic devices. Nature Physics, 2018, 14, 220-228.	6.5	298
59	Shape anisotropy revisited in single-digit nanometer magnetic tunnel junctions. Nature Communications, 2018, 9, 663.	5.8	141
60	Time and spatial evolution of spinâ€“orbit torque-induced magnetization switching in W/CoFeB/MgO structures with various sizes. Japanese Journal of Applied Physics, 2018, 57, 04FN02.	0.8	12
61	Electric-field effect on magnetic anisotropy in Pt/Co/Pd/MgO structures deposited on GaAs and Si substrates. Applied Physics Express, 2018, 11, 013003.	1.1	13
62	Temperature dependence of ferromagnetic resonance spectra of permalloy on (Bi_{1â^'} <i>) Tj ETQq0 0 0 rgBT /Overlock 10 T Physics, 2018, 57, 020302.	0.8	4
63	Electric-field effect on the easy cone angle of the easy-cone state in CoFeB/MgO investigated by ferromagnetic resonance. Applied Physics Letters, 2018, 112, .	1.5	13
64	Free-layer size dependence of anisotropy field in nanoscale CoFeB/MgO magnetic tunnel junctions. Applied Physics Express, 2018, 11, 043001.	1.1	6
65	Nonvolatile Memory Devices With Magnetic Nanowires Controlled by Spin-Transfer and Spin-Orbit Torques. , 2018, , .		1
66	Scalability and wide temperature range operation of spin-orbit torque switching devices using Co/Pt multilayer nanowires. Applied Physics Letters, 2018, 113, .	1.5	10
67	High thermal tolerance synthetic ferrimagnetic reference layer with modified buffer layer by ion irradiation for perpendicular anisotropy magnetic tunnel junctions.. , 2018, , .		0
68	Angle dependent magnetoresistance in heterostructures with antiferromagnetic and non-magnetic metals. Applied Physics Letters, 2018, 113, .	1.5	13
69	Evaluation of energy barrier of CoFeB/MgO magnetic tunnel junctions with perpendicular easy axis using retention time measurement. Japanese Journal of Applied Physics, 2018, 57, 04FN08.	0.8	20
70	Temperature-dependent properties of CoFeB/MgO thin films: Experiments versus simulations. Physical Review B, 2018, 98, .	1.1	46
71	An effect of capping-layer material on interfacial anisotropy and thermal stability factor of MgO/CoFeB/Ta/CoFeB/MgO/capping-layer structure. Applied Physics Letters, 2018, 113, 172401.	1.5	4
72	Perspective: Spintronic synapse for artificial neural network. Journal of Applied Physics, 2018, 124, .	1.1	67

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73	Preface to Special Topic: New Physics and Materials for Neuromorphic Computation. Journal of Applied Physics, 2018, 124, .	1.1	7
74	Characterization of spinâ€“orbit torque-controlled synapse device for artificial neural network applications. Japanese Journal of Applied Physics, 2018, 57, 1002B2.	0.8	17
75	Non-linear variation of domain period under electric field in demagnetized CoFeB/MgO stacks with perpendicular easy axis. Applied Physics Letters, 2018, 112, .	1.5	5
76	Spin-orbit torques in high-resistivity-W/CoFeB/MgO. Applied Physics Letters, 2018, 112, .	1.5	77
77	Fabrication and characterization of sub-micron scale hall devices from 2-dimensional electron gas at the heterostrutcure of GaAs/AlGaAs. AIP Conference Proceedings, 2018, , .	0.3	1
78	Evidence for Ferromagnetic Clusters in the Colossal-Magnetoresistance Material <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>EuB</mml:mi></mml:mrow><mml:mrow><mml:mn>6</mml:mn></m Physical Review Letters, 2018, 120, 257201.	2.9	33
79	MTJ-based nonvolatile logic LSI for ultra low-power and highly dependable computing. , 2018, , .		1
80	Origin of variation of shift field via annealing at 400Â°C in a perpendicular-anisotropy magnetic tunnel junction with [Co/Pt]-multilayers based synthetic ferrimagnetic reference layer. AIP Advances, 2017, 7, .	0.6	9
81	Damping constant in a free layer in nanoscale CoFeB/MgO magnetic tunnel junctions investigated by homodyne-detected ferromagnetic resonance. Applied Physics Express, 2017, 10, 013001.	1.1	9
82	Magnetic domain-wall creep driven by field and current in Ta/CoFeB/MgO. AIP Advances, 2017, 7, .	0.6	10
83	Ferromagnetic resonance spectra of Py deposited on (Bi1-xSbx)2Te3. AIP Advances, 2017, 7, .	0.6	6
84	Device-size dependence of field-free spin-orbit torque induced magnetization switching in antiferromagnet/ferromagnet structures. Applied Physics Letters, 2017, 110, .	1.5	66
85	Atomic structure and electronic properties of MgO grain boundaries in tunnelling magnetoresistive devices. Scientific Reports, 2017, 7, 45594.	1.6	35
86	Impact of Tungsten Sputtering Condition on Magnetic and Transport Properties of Double-MgO Magnetic Tunneling Junction With CoFeB/W/CoFeB Free Layer. IEEE Transactions on Magnetics, 2017, 53, 1-4.	1.2	17
87	Stack Structure Dependence of Magnetic Properties of PtMn/[Co/Ni] Films for Spin-Orbit Torque Switching Device. IEEE Transactions on Magnetics, 2017, 53, 1-4.	1.2	11
88	Electric-field-induced magnetization switching in CoFeB/MgO magnetic tunnel junctions. Japanese Journal of Applied Physics, 2017, 56, 0802A3.	0.8	2
89	Annealing temperature dependence of magnetic properties of CoFeB/MgO stacks on different buffer layers. Japanese Journal of Applied Physics, 2017, 56, 0802B2.	0.8	14
90	Magnetization switching schemes for nanoscale three-terminal spintronics devices. Japanese Journal of Applied Physics, 2017, 56, 0802A1.	0.8	40

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91	Design of a variationâ€resilient singleâ€ended nonâ€volatile sixâ€input lookup table circuit with a redundantâ€magnetic tunnel junctionâ€based active load for smart Internetâ€ofâ€things applications. Electronics Letters, 2017, 53, 456-458.	0.5	5
92	Magnetization dynamics and its scattering mechanism in thin CoFeB films with interfacial anisotropy. Proceedings of the National Academy of Sciences of the United States of America, 2017, 114, 3815-3820.	3.3	50
93	Analogue spinâ€“orbit torque device for artificial-neural-network-based associative memory operation. Applied Physics Express, 2017, 10, 013007.	1.1	146
94	A spin transfer torque magnetoresistance random access memory-based high-density and ultralow-power associative memory for fully data-adaptive nearest neighbor search with current-mode similarity evaluation and time-domain minimum searching. Japanese Journal of Applied Physics, 2017, 56, 04CF08.	0.8	2
95	Magnetic-field-angle dependence of coercivity in CoFeB/MgO magnetic tunnel junctions with perpendicular easy axis. Applied Physics Letters, 2017, 111, .	1.5	18
96	Electric-field effect on spin-wave resonance in a nanoscale CoFeB/MgO magnetic tunnel junction. Applied Physics Letters, 2017, 111, .	1.5	16
97	Spintronics based random access memory: a review. Materials Today, 2017, 20, 530-548.	8.3	689
98	Spin-orbit torque induced magnetization switching in Co/Pt multilayers. Applied Physics Letters, 2017, 111, .	1.5	26
99	Magnetic and transport properties of Sb₂Te₃ doped with high concentration of Cr. Applied Physics Express, 2017, 10, 103001.	1.1	17
100	Magnetic tunnel junctions with perpendicular easy axis at junction diameter of less than 20 nm. Japanese Journal of Applied Physics, 2017, 56, 0802A6.	0.8	17
101	Magnetic properties of FeV/MgO-based structures. Applied Physics Express, 2017, 10, 083001.	1.1	3
102	Three-terminal spintronics devices for CMOS integration. , 2017, , .		0
103	Spin-orbit torques and Dzyaloshinskii-Moriya interaction in PtMn/[Co/Ni] heterostructures. Applied Physics Letters, 2017, 111, .	1.5	15
104	Fast neutron tolerance of the perpendicular-anisotropy CoFeBâ€“MgO magnetic tunnel junctions with junction diameters between 46 and 64 nm. Japanese Journal of Applied Physics, 2017, 56, 0802B3.	0.8	4
105	Current-induced magnetization switching in a nano-scale CoFeB-MgO magnetic tunnel junction under in-plane magnetic field. AIP Advances, 2017, 7, 055927.	0.6	7
106	Fabrication of a magnetic-tunnel-junction-based nonvolatile logic-in-memory LSI with content-aware write error masking scheme achieving 92% storage capacity and 79% power reduction. Japanese Journal of Applied Physics, 2017, 56, 04CN01.	0.8	7
107	Soft errors in 10-nm-scale magnetic tunnel junctions exposed to high-energy heavy-ion radiation. Japanese Journal of Applied Physics, 2017, 56, 0802B4.	0.8	17
108	Use of analog spintronics device in performing neuro-morphic computing functions. , 2017, , .		1

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109	Magnetic and Free-Layer Properties of MgO/(Co)FeB/MgO Structures: Dependence on CoFeB Composition. IEEE Magnetics Letters, 2017, 8, 1-3.	0.6	16
110	Impact of sputtering condition for tungsten on magnetic and transport properties of magnetic tunneling junction with CoFeB/W/CoFeB free layer. , 2017, , .		0
111	Magnetization Reversal by Field and Current Pulses in Elliptic CoFeB/MgO Tunnel Junctions With Perpendicular Easy Axis. IEEE Magnetics Letters, 2016, 7, 1-4.	0.6	13
112	Critical role of W deposition condition on spin-orbit torque induced magnetization switching in nanoscale W/CoFeB/MgO. Applied Physics Letters, 2016, 109, .	1.5	69
113	Stochastic behavior-considered VLSI CAD environment for MTJ/MOS-hybrid microprocessor design. , 2016, , .		4
114	Electric field control of Skyrmions in magnetic nanodisks. Applied Physics Letters, 2016, 108, .	1.5	53
115	Peculiar temperature dependence of electric-field effect on magnetic anisotropy in Co/Pd/MgO system. Applied Physics Letters, 2016, 109, .	1.5	34
116	Effect of electric-field modulation of magnetic parameters on domain structure in MgO/CoFeB. AIP Advances, 2016, 6, .	0.6	27
117	Electric-field-induced magnetization switching in CoFeB/MgO magnetic tunnel junctions with high junction resistance. Applied Physics Letters, 2016, 108, .	1.5	84
118	An Overview of Nonvolatile Emerging Memoriesâ€" Spintronics for Working Memories. IEEE Journal on Emerging and Selected Topics in Circuits and Systems, 2016, 6, 109-119.	2.7	121
119	Current-induced domain wall motion in magnetic nanowires with various widths down to less than 20 nm. Japanese Journal of Applied Physics, 2016, 55, 04EN01.	0.8	5
120	Three-terminal spintronics devices for integrated circuits. , 2016, , .		0
121	A sub-ns three-terminal spin-orbit torque induced switching device. , 2016, , .		29
122	Free- and reference-layer magnetization modes versus in-plane magnetic field in a magnetic tunnel junction with perpendicular magnetic easy axis. Physical Review B, 2016, 94, .	1.1	4
123	Scanning the Issue. Proceedings of the IEEE, 2016, 104, 1782-1786.	16.4	33
124	Standby-Power-Free Integrated Circuits Using MTJ-Based VLSI Computing. Proceedings of the IEEE, 2016, 104, 1844-1863.	16.4	102
125	Fermi level position, Coulomb gap and Dresselhaus splitting in (Ga,Mn)As. Scientific Reports, 2016, 6, 27266.	1.6	24
126	Study on initial current leakage spots in CoFeB-capped MgO tunnel barrier by conductive atomic force microscopy. Japanese Journal of Applied Physics, 2016, 55, 04EE05.	0.8	5

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127	Temperature dependence of in-plane magnetic anisotropy and anisotropic magnetoresistance in (Ga,Mn)As codoped with Li. Applied Physics Letters, 2016, 108, .	1.5	7
128	A 600-ÂµW ultra-low-power associative processor for image pattern recognition employing magnetic tunnel junction-based nonvolatile memories with autonomic intelligent power-gating scheme. Japanese Journal of Applied Physics, 2016, 55, 04EF15.	0.8	14
129	Demonstration of Yield Improvement for On-Via MTJ Using a 2-Mbit 1T-1MTJ STT-MRAM Test Chip. , 2016, , .		9
130	Magnetic Properties of CoFeBâ€“MgO Stacks With Different Buffer-Layer Materials (Ta or Mo). IEEE Transactions on Magnetics, 2016, 52, 1-4.	1.2	16
131	Adiabatic spin-transfer-torque-induced domain wall creep in a magnetic metal. Nature Physics, 2016, 12, 333-336.	6.5	43
132	A spinâ€“orbit torque switching scheme with collinear magnetic easy axis and current configuration. Nature Nanotechnology, 2016, 11, 621-625.	15.6	466
133	Magnetization switching by spinâ€“orbit torque in an antiferromagnetâ€“ferromagnet bilayer system. Nature Materials, 2016, 15, 535-541.	13.3	782
134	Atomic-Scale Structure and Local Chemistry of CoFeBâ€“MgO Magnetic Tunnel Junctions. Nano Letters, 2016, 16, 1530-1536.	4.5	85
135	Improvement of Thermal Tolerance of CoFeBâ€“MgO Perpendicular-Anisotropy Magnetic Tunnel Junctions by Controlling Boron Composition. IEEE Transactions on Magnetics, 2016, 52, 1-4.	1.2	17
136	Current-Induced Magnetization Switching of CoFeB/Ta/[Co/Pd (Pt)]-Multilayers in Magnetic Tunnel Junctions With Perpendicular Anisotropy. IEEE Transactions on Magnetics, 2016, 52, 1-4.	1.2	7
137	Magnetic stray-field studies of a single Cobalt nanoelement as a component of the building blocks of artificial square spin ice. Journal of Magnetism and Magnetic Materials, 2016, 400, 206-212.	1.0	12
138	Proposal and demonstration of a new spin-orbit torque induced switching device. , 2015, , .		2
139	Electric-Field Modulation of Damping Constant in a Ferromagnetic Semiconductor (Ga,Mn)As. Physical Review Letters, 2015, 115, 057204.	2.9	29
140	Dependence of magnetic properties of MgO/CoFeB/Ta stacks on CoFeB and Ta thicknesses. Japanese Journal of Applied Physics, 2015, 54, 04DM04.	0.8	9
141	Vertical electric field induced suppression of fine structure splitting of excited state excitons in a single GaAs/AlGaAs island quantum dots. Applied Physics Letters, 2015, 107, 123102.	1.5	2
142	Electric-field induced nonlinear ferromagnetic resonance in a CoFeB/MgO magnetic tunnel junction. Applied Physics Letters, 2015, 107, .	1.5	15
143	Temperature dependence of energy barrier in CoFeB-MgO magnetic tunnel junctions with perpendicular easy axis. Applied Physics Letters, 2015, 107, .	1.5	27
144	Noise spectroscopy studies of GaAs/AlGaAs hall devices for optimizing micro- and nano-scale magnetic measurements. , 2015, , .		1

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145	Properties of perpendicular-anisotropy magnetic tunnel junctions fabricated over the bottom electrode contact. Japanese Journal of Applied Physics, 2015, 54, 04DM06.	0.8	5
146	Power-gated 32 bit microprocessor with a power controller circuit activated by deep-sleep-mode instruction achieving ultra-low power operation. Japanese Journal of Applied Physics, 2015, 54, 04DE08.	0.8	8
147	Thermal stability of a magnetic domain wall in nanowires. Physical Review B, 2015, 91, .	1.1	21
148	Control of magnetism by electric fields. Nature Nanotechnology, 2015, 10, 209-220.	15.6	741
149	Diffusion behaviors observed on the surface of CoFeB film after the natural oxidation and the annealing. , 2015, , .		0
150	1T1MTJ STT-MRAM Cell Array Design with an Adaptive Reference Voltage Generator for Improving Device Variation Tolerance. , 2015, , .		13
151	10 nmphi perpendicular-anisotropy CoFeB-MgO magnetic tunnel junction with over 400Â°C high thermal tolerance by boron diffusion control. , 2015, , .		17
152	Driving Force in Diffusion and Redistribution of Reducing Agents During Redox Reaction on the Surface of CoFeB Film. IEEE Transactions on Magnetics, 2015, 51, 1-4.	1.2	1
153	CoFeB Thickness Dependence of Damping Constants for Single and Double CoFeB-MgO Interface Structures. IEEE Magnetics Letters, 2015, 6, 1-3.	0.6	31
154	Temperature dependence of lattice parameter of (Ga,Mn)As on GaAs substrate. Japanese Journal of Applied Physics, 2015, 54, 098003.	0.8	2
155	Localized precessional mode of domain wall controlled by magnetic field and dc current. Applied Physics Express, 2015, 8, 023003.	1.1	4
156	In-plane anisotropy of a nano-scaled magnetic tunnel junction with perpendicular magnetic easy axis. Japanese Journal of Applied Physics, 2015, 54, 04DM03.	0.8	5
157	Ferromagnetic resonance in nanoscale CoFeB/MgO magnetic tunnel junctions. Journal of Applied Physics, 2015, 117, 17B708.	1.1	14
158	Evidence of a reduction reaction of oxidized iron/cobalt by boron atoms diffused toward naturally oxidized surface of CoFeB layer during annealing. Applied Physics Letters, 2015, 106, 142407.	1.5	11
159	Nanocluster building blocks of artificial square spin ice: Stray-field studies of thermal dynamics. Journal of Applied Physics, 2015, 117, .	1.1	13
160	Inverse spin Hall effect in Pt/(Ga,Mn)As. Applied Physics Letters, 2015, 106, 222405.	1.5	4
161	Three-terminal spintronics memory devices with perpendicular anisotropy. , 2015, , .		1
162	Spin-orbit torque induced magnetization switching in nano-scale Ta/CoFeB/MgO. Applied Physics Letters, 2015, 107, .	1.5	167

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163	Fabrication of a 3000-6-input-LUTs embedded and block-level power-gated nonvolatile FPGA chip using p-MTJ-based logic-in-memory structure. , 2015, , .		6
164	Ferromagnetic resonance of Py deposited on ZnO grown by molecular beam epitaxy. Japanese Journal of Applied Physics, 2015, 54, 093001.	0.8	4
165	Challenge of MTJ-based nonvolatile logic-in-memory architecture for ultra low-power and highly dependable VLSI computing. , 2015, , .		2
166	Nonvolatile Logic-in-Memory LSI Using Cycle-Based Power Gating and its Application to Motion-Vector Prediction. IEEE Journal of Solid-State Circuits, 2015, 50, 476-489.	3.5	53
167	Magnetic Semiconductors. , 2015, , 649-682.		0
168	Process-induced damage and its recovery for a CoFeBâ€“MgO magnetic tunnel junction with perpendicular magnetic easy axis. Japanese Journal of Applied Physics, 2014, 53, 103001.	0.8	17
169	Distribution of critical current density for magnetic domain wall motion. Journal of Applied Physics, 2014, 115, 17D508.	1.1	3
170	Wide operational margin capability of 1 kbit spin-transfer-torque memory array chip with 1-PMOS and 1-bottom-pin-magnetic-tunnel-junction type cell. Japanese Journal of Applied Physics, 2014, 53, 04ED13.	0.8	7
171	Challenge of MOS/MTJ-hybrid nonvolatile logic-in-memory architecture in dark-silicon era. , 2014, , .		6
172	Magnetic anisotropy in Ta/CoFeB/MgO investigated by x-ray magnetic circular dichroism and first-principles calculation. Applied Physics Letters, 2014, 105, .	1.5	47
173	Material Stack Design With High Tolerance to Process-Induced Damage in Domain Wall Motion Device. IEEE Transactions on Magnetics, 2014, 50, 1-4.	1.2	3
174	Perpendicular-anisotropy CoFeB-MgO based magnetic tunnel junctions scaling down to 1X nm. , 2014, , .		20
175	Strain and origin of inhomogeneous broadening probed by optically detected nuclear magnetic resonance in a (110) GaAs quantum well. Physical Review B, 2014, 89, .	1.1	6
176	Properties of (Ga,Mn)As codoped with Li. Applied Physics Letters, 2014, 104, 222408.	1.5	1
177	Properties of magnetic tunnel junctions with a MgO/CoFeB/Ta/CoFeB/MgO recording structure down to junction diameter of 11â€‰nm. Applied Physics Letters, 2014, 105, .	1.5	240
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